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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	120MHz
Connectivity	CANbus, EBI/EMI, I²C, IrDA, SD, SPI, UART/USART, USB, USB OTG
Peripherals	DMA, I²S, LVD, POR, PWM, WDT
Number of I/O	100
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	256K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 41x16b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	144-LQFP
Supplier Device Package	144-LQFP (20x20)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mk24fn1m0vlq12

2.2.1 Voltage and current operating requirements

Table 1. Voltage and current operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
V_{DD}	Supply voltage	1.71	3.6	V	
V_{DDA}	Analog supply voltage	1.71	3.6	V	
$V_{DD} – V_{DDA}$	V_{DD}-to-V_{DDA} differential voltage	–0.1	0.1	V	
$V_{SS} – V_{SSA}$	V_{SS}-to-V_{SSA} differential voltage	–0.1	0.1	V	
V_{BAT}	RTC battery supply voltage	1.71	3.6	V	
V_{IH}	Input high voltage • $2.7 V \leq V_{DD} \leq 3.6 V$ • $1.7 V \leq V_{DD} \leq 2.7 V$	 $0.7 \times V_{DD}$ $0.75 \times V_{DD}$	 — —	 V V	
V_{IL}	Input low voltage • $2.7 V \leq V_{DD} \leq 3.6 V$ • $1.7 V \leq V_{DD} \leq 2.7 V$	 — —	 $0.35 \times V_{DD}$ $0.3 \times V_{DD}$	 V V	
V_{HYS}	Input hysteresis	$0.06 \times V_{DD}$	—	V	
I_{ICDIO}	Digital pin negative DC injection current — single pin • $V_{IN} < V_{SS}$-0.3V	-5	—	mA	1
I_{ICAIO}	Analog[2], EXTAL, and XTAL pin DC injection current — single pin • $V_{IN} < V_{SS}$-0.3V (Negative current injection) • $V_{IN} > V_{DD}$+0.3V (Positive current injection)	 -5 —	 — +5	mA	3
I_{ICcont}	Contiguous pin DC injection current —regional limit, includes sum of negative injection currents or sum of positive injection currents of 16 contiguous pins • Negative current injection • Positive current injection	 -25 —	 — +25	mA	
V_{ODPU}	Open drain pullup voltage level	V_{DD}	V_{DD}	V	4
V_{RAM}	V_{DD} voltage required to retain RAM	1.2	—	V	
V_{RFVBAT}	V_{BAT} voltage required to retain the VBAT register file	V_{POR_VBAT}	—	V	

1. All 5 V tolerant digital I/O pins are internally clamped to V_{SS} through an ESD protection diode. There is no diode connection to V_{DD}. If V_{IN} is less than V_{DIO_MIN}, a current limiting resistor is required. If V_{IN} greater than V_{DIO_MIN} (=VSS-0.3V) is observed, then there is no need to provide current limiting resistors at the pads. The negative DC injection current limiting resistor is calculated as $R=(V_{DIO\_MIN}-V_{IN})/|I_{ICDIO}|$.
2. Analog pins are defined as pins that do not have an associated general purpose I/O port function. Additionally, EXTAL and XTAL are analog pins.
3. All analog pins are internally clamped to V_{SS} and V_{DD} through ESD protection diodes. If V_{IN} is less than V_{AIO_MIN} or greater than V_{AIO_MAX}, a current limiting resistor is required. The negative DC injection current limiting resistor is calculated as $R=(V_{AIO\_MIN}-V_{IN})/|I_{ICAIO}|$. The positive injection current limiting resistor is calculated as $R=(V_{IN}-V_{AIO\_MAX})/|I_{ICAIO}|$. Select the larger of these two calculated resistances if the pin is exposed to positive and negative injection currents.
4. Open drain outputs must be pulled to VDD.

2.2.2 LVD and POR operating requirements

Table 2. V_{DD} supply LVD and POR operating requirements

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{POR}	Falling VDD POR detect voltage	0.8	1.1	1.5	V	
V_{LVDH}	Falling low-voltage detect threshold — high range (LVDV=01)	2.48	2.56	2.64	V	
	Low-voltage warning thresholds — high range					1
V_{LVW1H}	• Level 1 falling (LVWV=00)	2.62	2.70	2.78	V	
V_{LVW2H}	• Level 2 falling (LVWV=01)	2.72	2.80	2.88	V	
V_{LVW3H}	• Level 3 falling (LVWV=10)	2.82	2.90	2.98	V	
V_{LVW4H}	• Level 4 falling (LVWV=11)	2.92	3.00	3.08	V	
V_{HYSH}	Low-voltage inhibit reset/recover hysteresis — high range	—	80	—	mV	
V_{LVDL}	Falling low-voltage detect threshold — low range (LVDV=00)	1.54	1.60	1.66	V	
	Low-voltage warning thresholds — low range					1
V_{LVW1L}	• Level 1 falling (LVWV=00)	1.74	1.80	1.86	V	
V_{LVW2L}	• Level 2 falling (LVWV=01)	1.84	1.90	1.96	V	
V_{LVW3L}	• Level 3 falling (LVWV=10)	1.94	2.00	2.06	V	
V_{LVW4L}	• Level 4 falling (LVWV=11)	2.04	2.10	2.16	V	
V_{HYSL}	Low-voltage inhibit reset/recover hysteresis — low range	—	60	—	mV	
V_{BG}	Bandgap voltage reference	0.97	1.00	1.03	V	
t_{LPO}	Internal low power oscillator period — factory trimmed	900	1000	1100	μs	

1. Rising threshold is the sum of falling threshold and hysteresis voltage

Table 3. VBAT power operating requirements

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{POR_VBAT}	Falling VBAT supply POR detect voltage	0.8	1.1	1.5	V	

2.2.3 Voltage and current operating behaviors

Table 4. Voltage and current operating behaviors

Symbol	Description	Min.	Max.	Unit	Notes
V_{OH}	Output high voltage — high drive strength				

Table continues on the next page...

2.2.5 Power consumption operating behaviors

NOTE

The maximum values represent characterized results equivalent to the mean plus three times the standard deviation (mean + 3 sigma).

Table 6. Power consumption operating behaviors

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I_{DDA}	Analog supply current	—	—	See note	mA	1
I_{DD_RUN}	Run mode current — all peripheral clocks disabled, code executing from flash • @ 1.8V • @ 3.0V	 — —	 31.1 31	 36.65 36.75	 mA mA	2

I_{DD_RUN}	Run mode current — all peripheral clocks enabled, code executing from flash
	• @ 1.8V
	• @ 3.0V
	  • @ 25°C
	  • @ 105°C
		
		—
		
		—
		—
			
			42.7
			
			40
			48.33
				
				48.35
				
				41.60
				51.50
					
					mA
					
					mA
					mA
						3, 4

I_{DD_WAIT}	Wait mode high frequency current at 3.0 V — all peripheral clocks disabled	—	17.9	—	mA	2
I_{DD_WAIT}	Wait mode reduced frequency current at 3.0 V — all peripheral clocks disabled	—	6.9	—	mA	5
I_{DD_VLPR}	Very-low-power run mode current at 3.0 V — all peripheral clocks disabled	—	1.0	—	mA	6
I_{DD_VLPR}	Very-low-power run mode current at 3.0 V — all peripheral clocks enabled	—	1.7	—	mA	7
I_{DD_VLPW}	Very-low-power wait mode current at 3.0 V — all peripheral clocks disabled	—	0.678	—	mA	8
I_{DD_STOP}	Stop mode current at 3.0 V • @ –40 to 25°C • @ 70°C • @ 105°C	 — — —	 0.49 1.18 3.0	 1.24 4.3 12.5	 mA mA mA	
I_{DD_VLPS}	Very-low-power stop mode current at 3.0 V • @ –40 to 25°C • @ 70°C • @ 105°C	 — — —	 57 291 927.3	 139.31 679.33 1869.85	 μA μA μA	
I_{DD_LLS}	Low leakage stop mode current at 3.0 V					9

Table continues on the next page...

Table 6. Power consumption operating behaviors (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
	• @ –40 to 25°C	—	5.8	10.48	μA	
	• @ 70°C	—	26.7	47.99	μA	
	• @ 105°C	—	114.9	196.49	μA	
I_{DD_VLLS3}	Very low-leakage stop mode 3 current at 3.0 V					
	• @ –40 to 25°C	—	4.4	5.54	μA	
	• @ 70°C	—	21	36.46	μA	
	• @ 105°C	—	90.2	150.17	μA	
I_{DD_VLLS2}	Very low-leakage stop mode 2 current at 3.0 V					
	• @ –40 to 25°C	—	2.1	2.34	μA	
	• @ 70°C	—	6.84	10.36	μA	
	• @ 105°C	—	29.4	46.74	μA	
I_{DD_VLLS1}	Very low-leakage stop mode 1 current at 3.0 V					
	• @ –40 to 25°C	—	0.817	0.86	μA	
	• @ 70°C	—	3.97	5.77	μA	
	• @ 105°C	—	21.3	33.99	μA	
I_{DD_VLLS0}	Very low-leakage stop mode 0 current at 3.0 V with POR detect circuit enabled					
	• @ –40 to 25°C	—	0.52	0.62	μA	
	• @ 70°C	—	3.67	5.7	μA	
	• @ 105°C	—	21.20	34.9	μA	
I_{DD_VLLS0}	Very low-leakage stop mode 0 current at 3.0 V with POR detect circuit disabled					
	• @ –40 to 25°C	—	0.339	0.412	μA	
	• @ 70°C	—	3.36	4.2	μA	
	• @ 105°C	—	20.3	29.9	μA	
I_{DD_VBAT}	Average current with RTC and 32 kHz disabled					
	• @ 1.8 V					
	• @ –40 to 25°C	—	0.16	0.19	μA	
	• @ 70°C	—	0.55	0.72	μA	
	• @ 105°C	—	2.5	3.68	μA	
	• @ 3.0 V					
	• @ –40 to 25°C	—	0.18	0.21	μA	
	• @ 70°C	—	0.66	0.86	μA	
	• @ 105°C	—	2.92	4.30	μA	

Table continues on the next page...

- No GPIOs toggled
- Code execution from flash with cache enabled
- For the ALLOFF curve, all peripheral clocks are disabled except FTFE

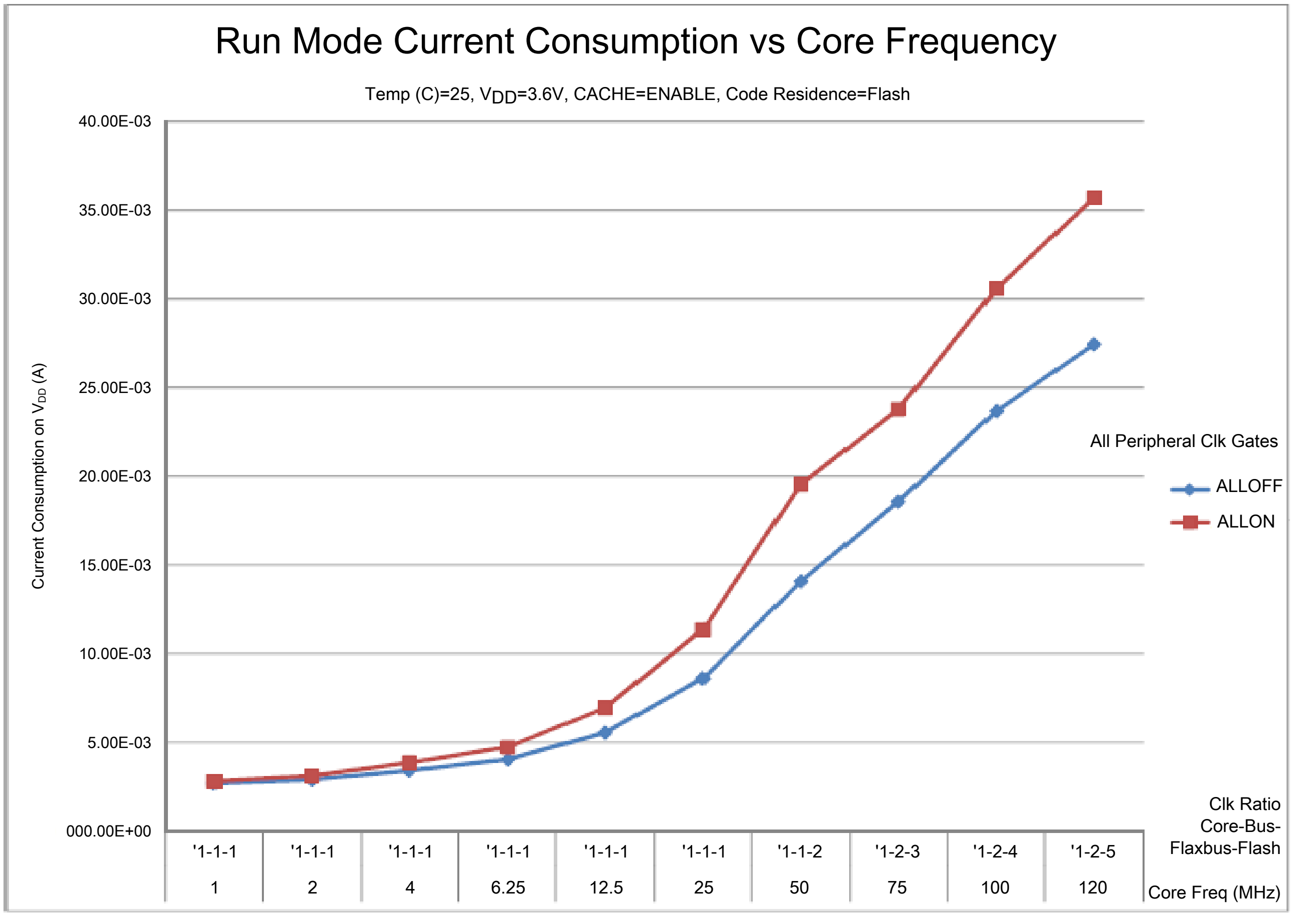

Figure 3. Run mode supply current vs. core frequency

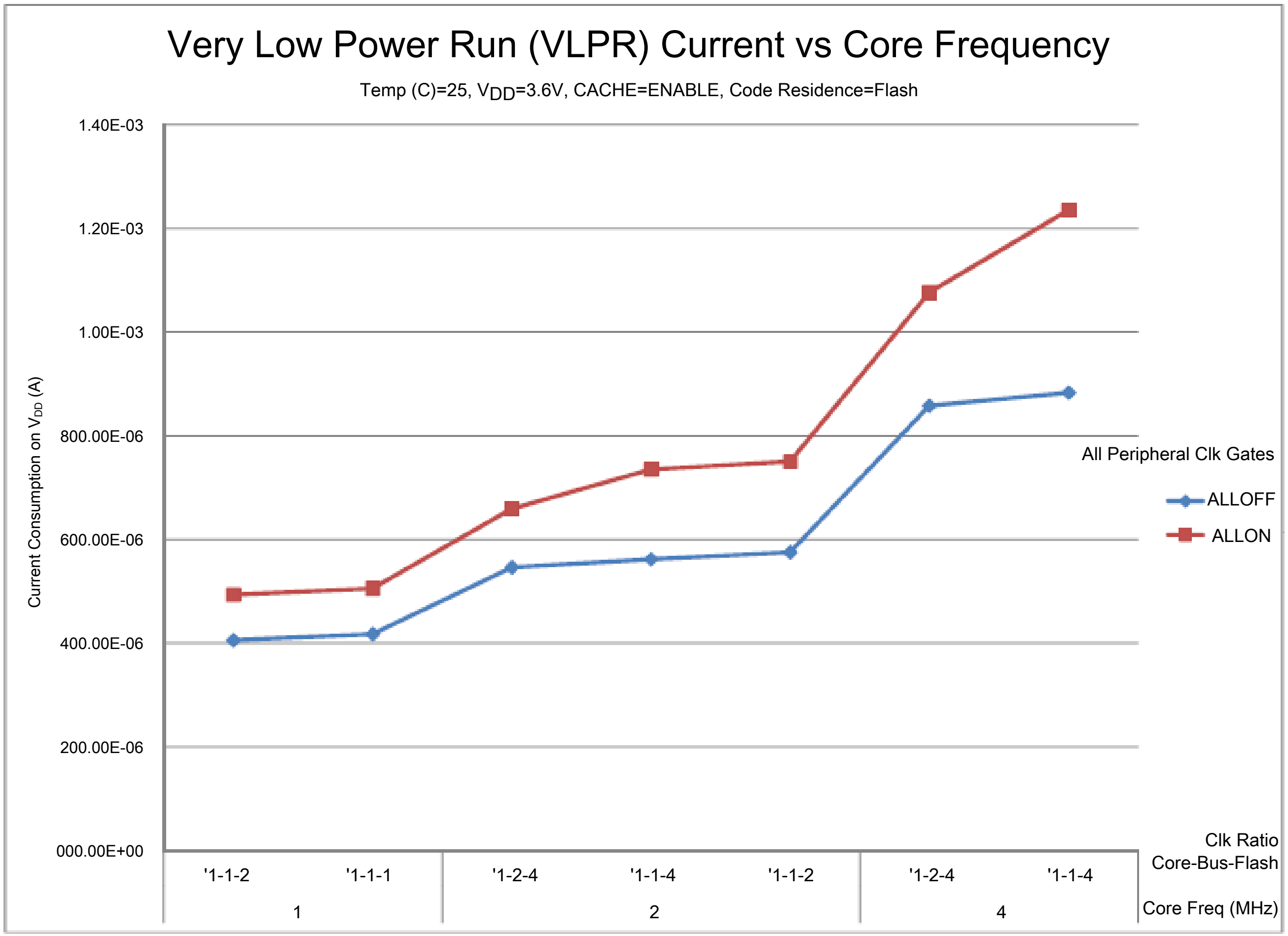

Figure 4. VLPR mode supply current vs. core frequency

2.2.6 EMC radiated emissions operating behaviors

Table 8. EMC radiated emissions operating behaviors

Symbol	Description	Frequency band (MHz)	Typ.	Unit	Notes
			144 LQFP		
V_{RE1}	Radiated emissions voltage, band 1	0.15–50	16	dBμV	1, 2
V_{RE2}	Radiated emissions voltage, band 2	50–150	22	dBμV	
V_{RE3}	Radiated emissions voltage, band 3	150–500	21	dBμV	
V_{RE4}	Radiated emissions voltage, band 4	500–1000	16	dBμV	
V_{RE_IEC}	IEC level	0.15–1000	L	—	2, 3

1. Determined according to IEC Standard 61967-1, *Integrated Circuits - Measurement of Electromagnetic Emissions, 150 kHz to 1 GHz Part 1: General Conditions and Definitions* and IEC Standard 61967-2, *Integrated Circuits - Measurement of Electromagnetic Emissions, 150 kHz to 1 GHz Part 2: Measurement of Radiated Emissions—TEM Cell and*

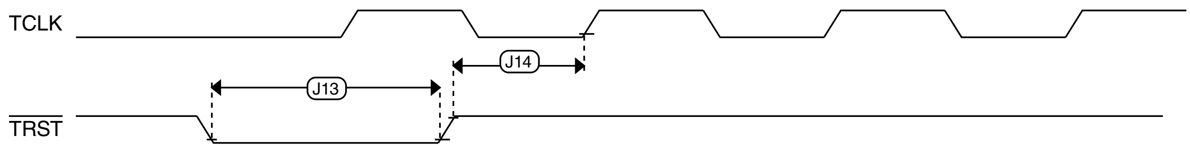

Figure 10. $\overline{TRST}$ timing

3.2 System modules

There are no specifications necessary for the device's system modules.

3.3 Clock modules

3.3.1 MCG specifications

Table 17. MCG specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
f_{ints_ft}	Internal reference frequency (slow clock) — factory trimmed at nominal VDD and 25 °C	—	32.768	—	kHz	
f_{ints_t}	Internal reference frequency (slow clock) — user trimmed	31.25	—	39.0625	kHz	
I_{ints}	Internal reference (slow clock) current	—	20	—	µA	
$\Delta_{fdco\_res\_t}$	Resolution of trimmed average DCO output frequency at fixed voltage and temperature — using SCTRIM and SCFTRIM	—	± 0.3	± 0.6	$\%f_{dco}$	1
$\Delta f_{dco\_res\_t}$	Resolution of trimmed average DCO output frequency at fixed voltage and temperature — using SCTRIM only	—	± 0.2	± 0.5	$\%f_{dco}$	1
Δf_{dco_t}	Total deviation of trimmed average DCO output frequency over voltage and temperature	—	± 0.5	± 2	$\%f_{dco}$	1, 2
Δf_{dco_t}	Total deviation of trimmed average DCO output frequency over fixed voltage and temperature range of 0–70°C	—	± 0.3	± 1	$\%f_{dco}$	1
f_{intf_ft}	Internal reference frequency (fast clock) — factory trimmed at nominal VDD and 25°C	—	4	—	MHz	
f_{intf_t}	Internal reference frequency (fast clock) — user trimmed at nominal VDD and 25 °C	3	—	5	MHz	
I_{intf}	Internal reference (fast clock) current	—	25	—	µA	

Table continues on the next page...

3.4.1.4 Reliability specifications

Table 26. NVM reliability specifications

Symbol	Description	Min.	Typ.[1]	Max.	Unit	Notes
	Program Flash					
$t_{nvmretp10k}$	Data retention after up to 10 K cycles	5	50	—	years	
$t_{nvmretp1k}$	Data retention after up to 1 K cycles	20	100	—	years	
$n_{nvmcycp}$	Cycling endurance	10 K	50 K	—	cycles	2

1. Typical data retention values are based on measured response accelerated at high temperature and derated to a constant 25°C use profile. Engineering Bulletin EB618 does not apply to this technology. Typical endurance defined in Engineering Bulletin EB619.
2. Cycling endurance represents number of program/erase cycles at -40°C ≤ T_j ≤ 125°C.

3.4.2 EzPort switching specifications

Table 27. EzPort switching specifications

Num	Description	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
EP1	EZP_CK frequency of operation (all commands except READ)	—	$f_{SYS}/2$	MHz
EP1a	EZP_CK frequency of operation (READ command)	—	$f_{SYS}/8$	MHz
EP2	$\overline{\text{EZP\_CS}}$ negation to next $\overline{\text{EZP\_CS}}$ assertion	2 x t_{EZP_CK}	—	ns
EP3	$\overline{\text{EZP\_CS}}$ input valid to EZP_CK high (setup)	5	—	ns
EP4	EZP_CK high to $\overline{\text{EZP\_CS}}$ input invalid (hold)	5	—	ns
EP5	EZP_D input valid to EZP_CK high (setup)	2	—	ns
EP6	EZP_CK high to EZP_D input invalid (hold)	5	—	ns
EP7	EZP_CK low to EZP_Q output valid	—	18	ns
EP8	EZP_CK low to EZP_Q output invalid (hold)	0	—	ns
EP9	$\overline{\text{EZP\_CS}}$ negation to EZP_Q tri-state	—	12	ns

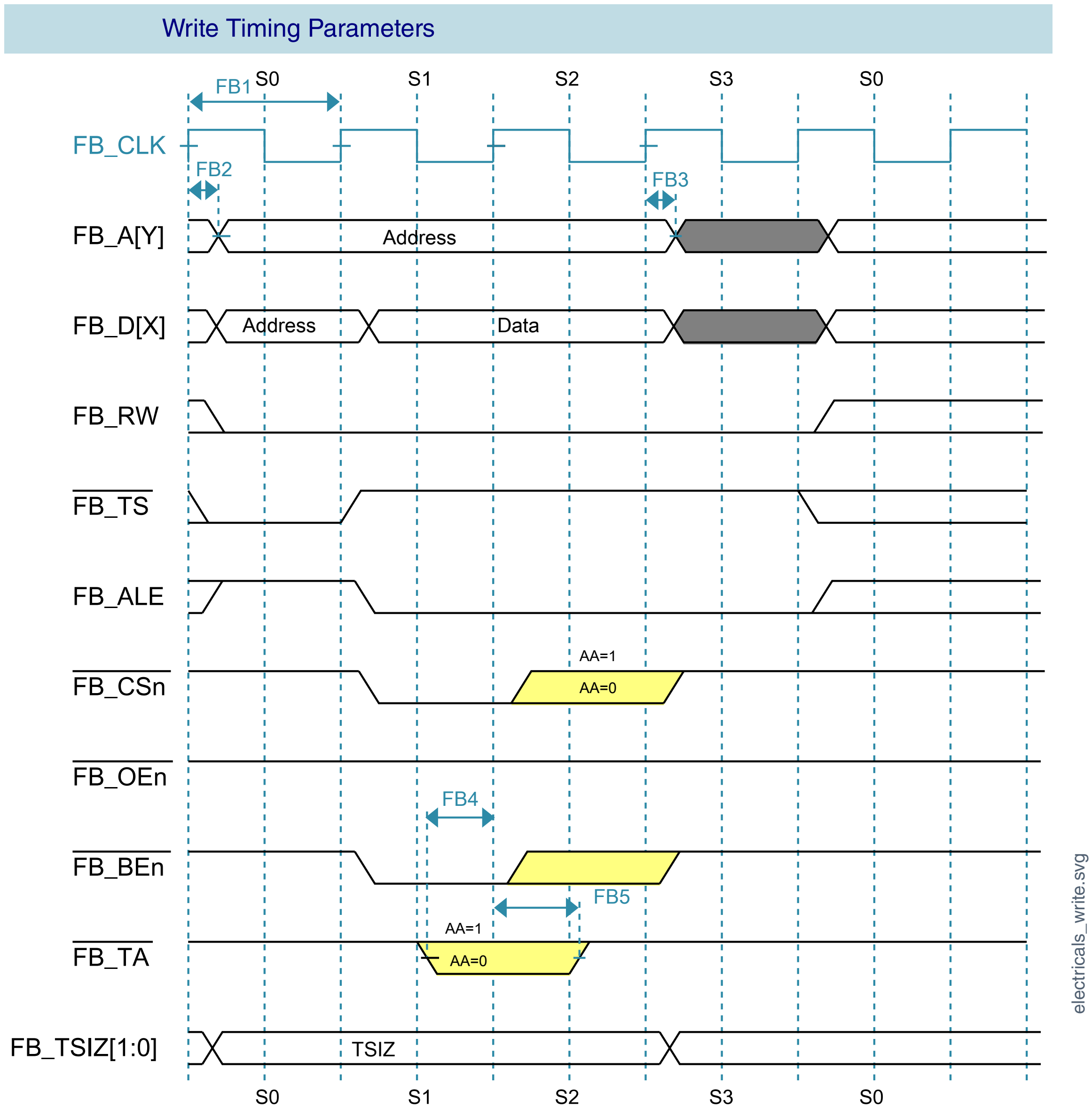

Figure 13. FlexBus write timing diagram

3.5 Security and integrity modules

There are no specifications necessary for the device's security and integrity modules.

3.6 Analog

1. Typical values assume V_{DDA} = 3.0 V, Temp = 25 °C, f_{ADCK} = 1.0 MHz, unless otherwise stated. Typical values are for reference only, and are not tested in production.
2. DC potential difference.
3. This resistance is external to MCU. To achieve the best results, the analog source resistance must be kept as low as possible. The results in this data sheet were derived from a system that had < 8 Ω analog source resistance. The R_{AS}/C_{AS} time constant should be kept to < 1 ns.
4. To use the maximum ADC conversion clock frequency, CFG2[ADHSC] must be set and CFG1[ADLPC] must be clear.
5. For guidelines and examples of conversion rate calculation, download the ADC calculator tool.

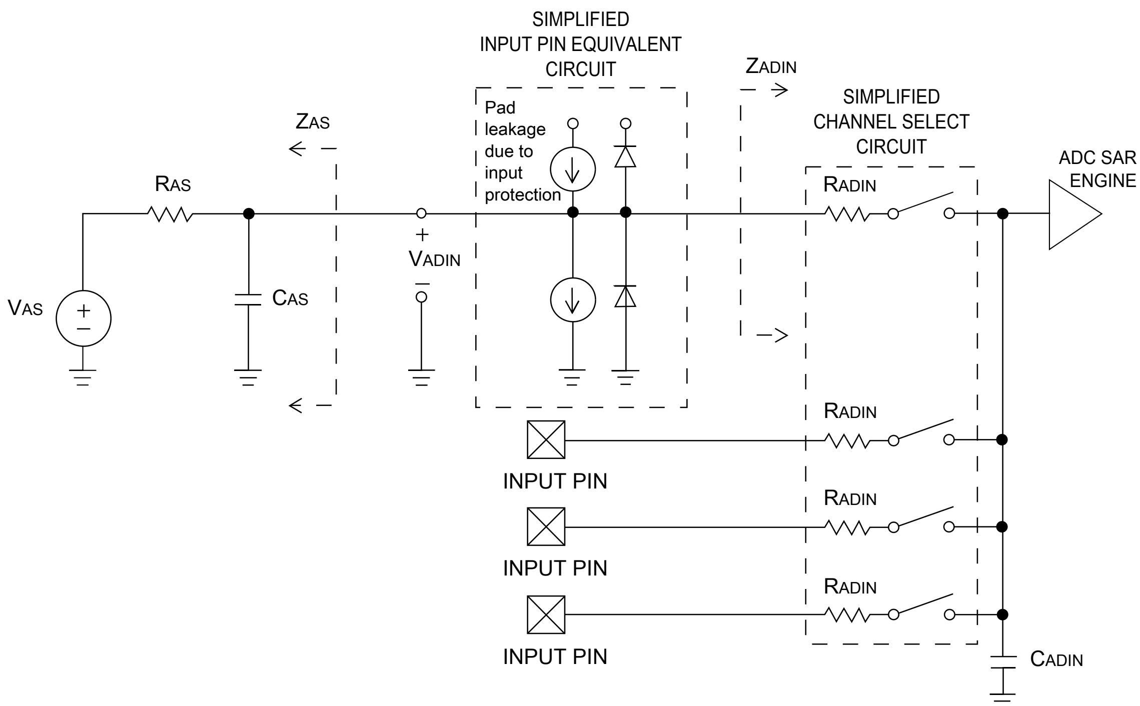

Figure 14. ADC input impedance equivalency diagram

3.6.1.2 16-bit ADC electrical characteristics

Table 31. 16-bit ADC characteristics ($V_{REFH} = V_{DDA}$, $V_{REFL} = V_{SSA}$)

Symbol	Description	Conditions[1]	Min.	Typ.[2]	Max.	Unit	Notes
I_{DDA_ADC}	Supply current		0.215	—	1.7	mA	3
f_{ADACK}	ADC asynchronous clock source	• ADLPC = 1, ADHSC = 0	1.2	2.4	3.9	MHz	$t_{ADACK} = 1/f_{ADACK}$
		• ADLPC = 1, ADHSC = 1	2.4	4.0	6.1	MHz	
		• ADLPC = 0, ADHSC = 0	3.0	5.2	7.3	MHz	
		• ADLPC = 0, ADHSC = 1	4.4	6.2	9.5	MHz	
	Sample Time	See Reference Manual chapter for sample times					

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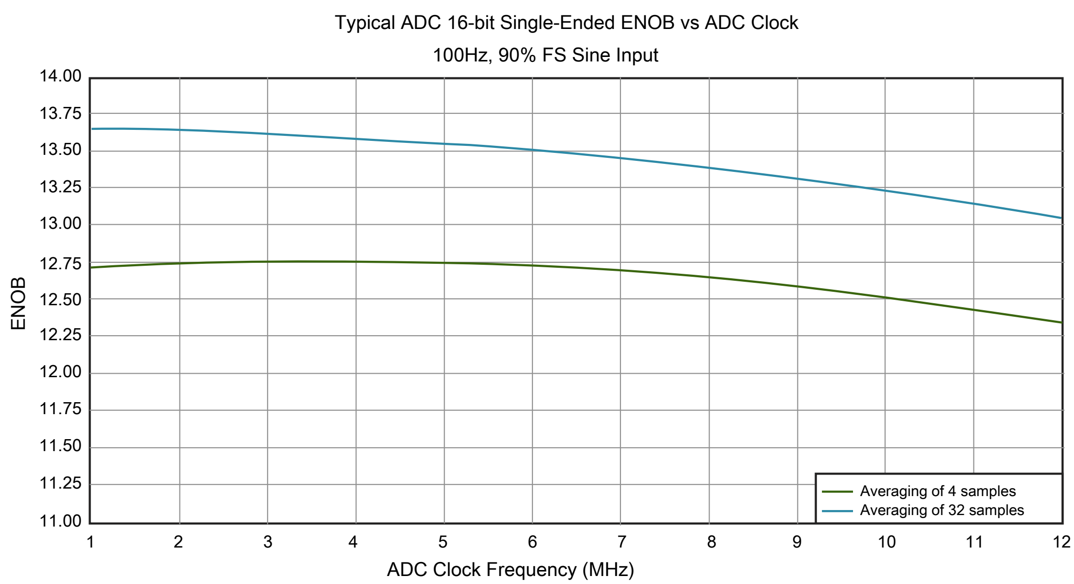

Figure 16. Typical ENOB vs. ADC_CLK for 16-bit single-ended mode

3.6.2 CMP and 6-bit DAC electrical specifications

Table 32. Comparator and 6-bit DAC electrical specifications

Symbol	Description	Min.	Typ.	Max.	Unit
V_{DD}	Supply voltage	1.71	—	3.6	V
I_{DDHS}	Supply current, High-speed mode (EN=1, PMODE=1)	—	—	200	μA
I_{DDLS}	Supply current, low-speed mode (EN=1, PMODE=0)	—	—	20	μA
V_{AIN}	Analog input voltage	V_{SS} – 0.3	—	V_{DD}	V
V_{AIO}	Analog input offset voltage	—	—	20	mV
V_H	Analog comparator hysteresis[1]				
	• CR0[HYSTCTR] = 00	—	5	—	mV
	• CR0[HYSTCTR] = 01	—	10	—	mV
	• CR0[HYSTCTR] = 10	—	20	—	mV
	• CR0[HYSTCTR] = 11	—	30	—	mV
V_{CMPOh}	Output high	V_{DD} – 0.5	—	—	V
V_{CMPOl}	Output low	—	—	0.5	V
t_{DHS}	Propagation delay, high-speed mode (EN=1, PMODE=1)	20	50	200	ns
t_{DLS}	Propagation delay, low-speed mode (EN=1, PMODE=0)	80	250	600	ns
	Analog comparator initialization delay[2]	—	—	40	μs
I_{DAC6b}	6-bit DAC current adder (enabled)	—	7	—	μA
INL	6-bit DAC integral non-linearity	–0.5	—	0.5	LSB[3]
DNL	6-bit DAC differential non-linearity	–0.3	—	0.3	LSB

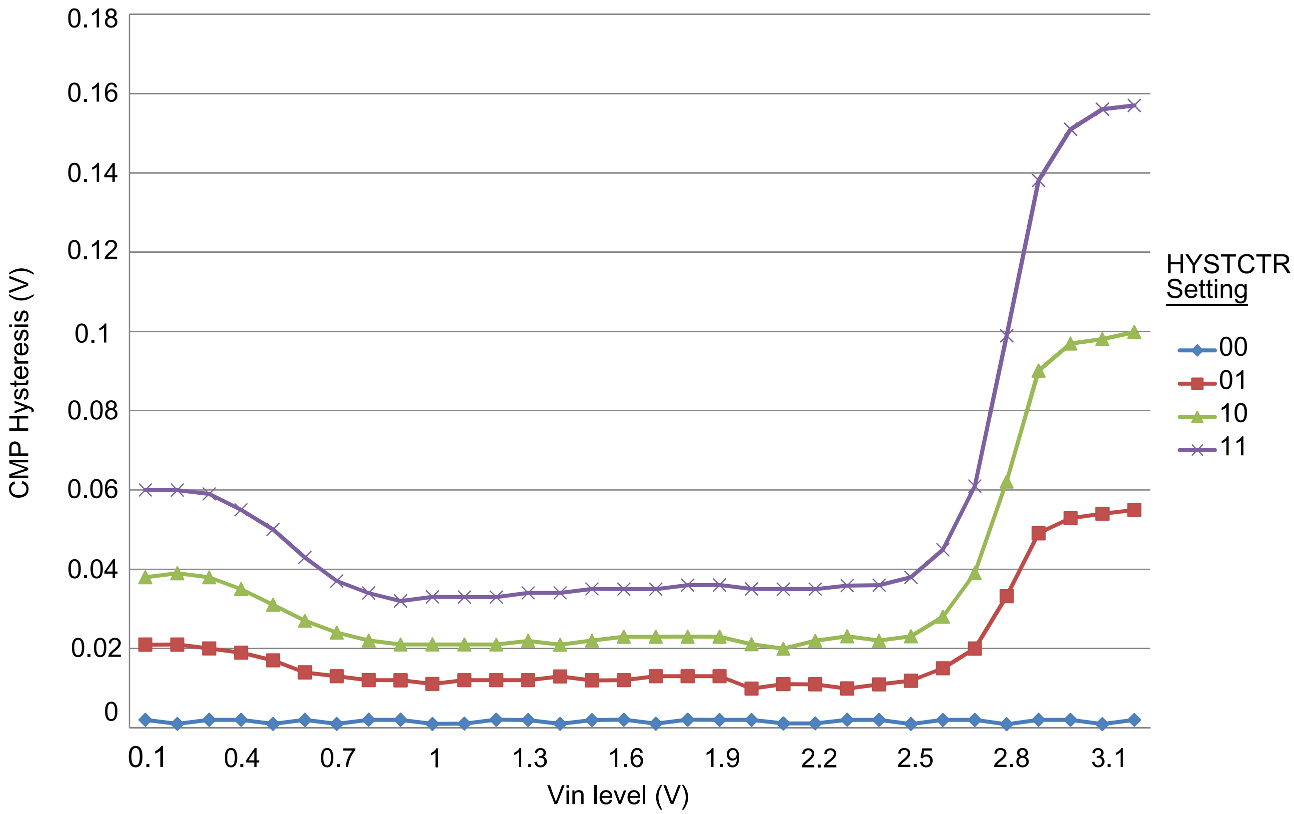

Figure 18. Typical hysteresis vs. Vin level (VDD = 3.3 V, PMODE = 1)

3.6.3 12-bit DAC electrical characteristics

3.6.3.1 12-bit DAC operating requirements

Table 33. 12-bit DAC operating requirements

Symbol	Desciption	Min.	Max.	Unit	Notes
V_{DDA}	Supply voltage	1.71	3.6	V	
V_{DACR}	Reference voltage	1.13	3.6	V	1
C_L	Output load capacitance	—	100	pF	2
I_L	Output load current	—	1	mA	

1. The DAC reference can be selected to be V_{DDA} or V_{REFH}.
2. A small load capacitance (47 pF) can improve the bandwidth performance of the DAC.

3.8.1 USB electrical specifications

The USB electricals for the USB On-the-Go module conform to the standards documented by the Universal Serial Bus Implementers Forum. For the most up-to-date standards, visit **usb.org**.

NOTE

The MCGPLLCLK meets the USB jitter and signaling rate specifications for certification with the use of an external clock/crystal for both Device and Host modes.

The MCGFLLCLK does not meet the USB jitter or signaling rate specifications for certification.

The IRC48M meets the USB jitter and signaling rate specifications for certification in Device mode when the USB clock recovery mode is enabled. It does not meet the USB signaling rate specifications for certification in Host mode operation.

3.8.2 USB DCD electrical specifications

Table 39. USB0 DCD electrical specifications

Symbol	Description	Min.	Typ.	Max.	Unit
V_{DP_SRC}	USB_DP source voltage (up to 250 μA)	0.5	—	0.7	V
V_{LGC}	Threshold voltage for logic high	0.8	—	2.0	V
I_{DP_SRC}	USB_DP source current	7	10	13	μA
I_{DM_SINK}	USB_DM sink current	50	100	150	μA
R_{DM_DWN}	D- pulldown resistance for data pin contact detect	14.25	—	24.8	kΩ
V_{DAT_REF}	Data detect voltage	0.25	0.33	0.4	V

3.8.3 USB VREG electrical specifications

Table 40. USB VREG electrical specifications

Symbol	Description	Min.	Typ.[1]	Max.	Unit	Notes
VREGIN	Input supply voltage	2.7	—	5.5	V	

Table continues on the next page...

Table 50. I2S/SAI master mode timing (continued)

Num.	Characteristic	Min.	Max.	Unit
S3	I2S_TX_BCLK/I2S_RX_BCLK cycle time (output)	80	—	ns
S4	I2S_TX_BCLK/I2S_RX_BCLK pulse width high/low	45%	55%	BCLK period
S5	I2S_TX_BCLK/I2S_RX_BCLK to I2S_TX_FS/ I2S_RX_FS output valid	—	15	ns
S6	I2S_TX_BCLK/I2S_RX_BCLK to I2S_TX_FS/ I2S_RX_FS output invalid	-1	—	ns
S7	I2S_TX_BCLK to I2S_TXD valid	—	15	ns
S8	I2S_TX_BCLK to I2S_TXD invalid	0	—	ns
S9	I2S_RXD/I2S_RX_FS input setup before I2S_RX_BCLK	22.5	—	ns
S10	I2S_RXD/I2S_RX_FS input hold after I2S_RX_BCLK	0	—	ns

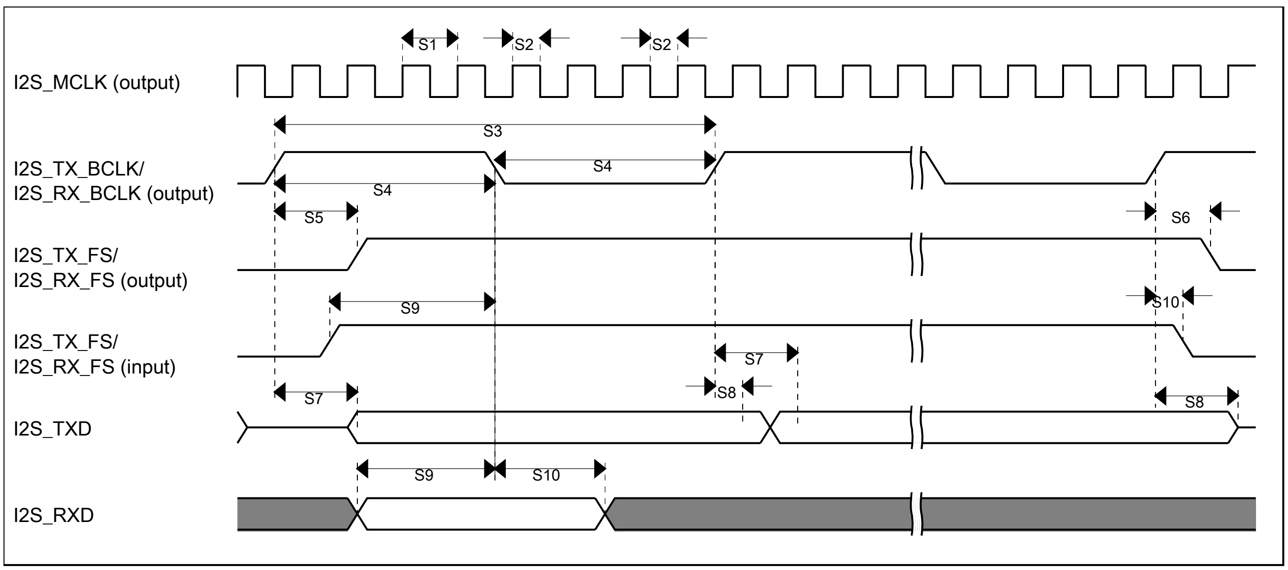

Figure 29. I2S/SAI timing — master modes

Table 51. I2S/SAI slave mode timing

Num.	Characteristic	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
S11	I2S_TX_BCLK/I2S_RX_BCLK cycle time (input)	80	—	ns
S12	I2S_TX_BCLK/I2S_RX_BCLK pulse width high/low (input)	45%	55%	MCLK period
S13	I2S_TX_FS/I2S_RX_FS input setup before I2S_TX_BCLK/I2S_RX_BCLK	7	—	ns
S14	I2S_TX_FS/I2S_RX_FS input hold after I2S_TX_BCLK/I2S_RX_BCLK	2	—	ns

Table continues on the next page...

Table 51. I2S/SAI slave mode timing (continued)

Num.	Characteristic	Min.	Max.	Unit
S15	I2S_TX_BCLK to I2S_TXD/I2S_TX_FS output valid	—	25.5	ns
S16	I2S_TX_BCLK to I2S_TXD/I2S_TX_FS output invalid	3	—	ns
S17	I2S_RXD setup before I2S_RX_BCLK	5.8	—	ns
S18	I2S_RXD hold after I2S_RX_BCLK	2	—	ns
S19	I2S_TX_FS input assertion to I2S_TXD output valid[1]	—	25	ns

1. Applies to first bit in each frame and only if the TCR4[FSE] bit is clear

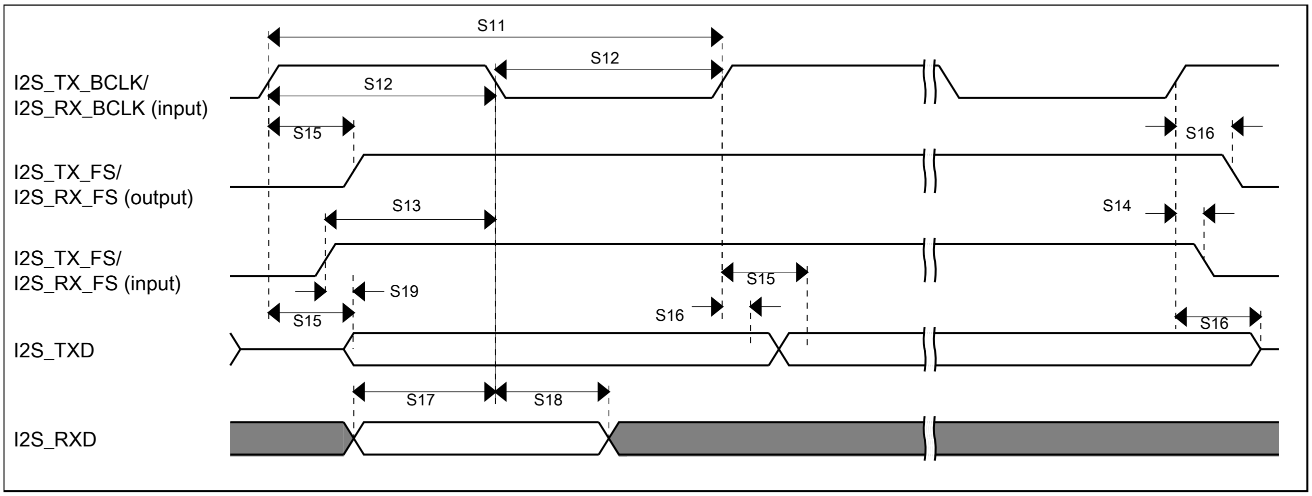

Figure 30. I2S/SAI timing — slave modes

3.8.10.2 VLPR, VLPW, and VLPS mode performance over the full operating voltage range

This section provides the operating performance over the full operating voltage for the device in VLPR, VLPW, and VLPS modes.

Table 52. I2S/SAI master mode timing in VLPR, VLPW, and VLPS modes (full voltage range)

Num.	Characteristic	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
S1	I2S_MCLK cycle time	62.5	—	ns
S2	I2S_MCLK pulse width high/low	45%	55%	MCLK period
S3	I2S_TX_BCLK/I2S_RX_BCLK cycle time (output)	250	—	ns
S4	I2S_TX_BCLK/I2S_RX_BCLK pulse width high/low	45%	55%	BCLK period
S5	I2S_TX_BCLK/I2S_RX_BCLK to I2S_TX_FS/ I2S_RX_FS output valid	—	45	ns

Table continues on the next page...

Table 52. I2S/SAI master mode timing in VLPR, VLPW, and VLPS modes (full voltage range) (continued)

Num.	Characteristic	Min.	Max.	Unit
S6	I2S_TX_BCLK/I2S_RX_BCLK to I2S_TX_FS/ I2S_RX_FS output invalid	0	—	ns
S7	I2S_TX_BCLK to I2S_TXD valid	—	45	ns
S8	I2S_TX_BCLK to I2S_TXD invalid		—	ns
S9	I2S_RXD/I2S_RX_FS input setup before I2S_RX_BCLK	45	—	ns
S10	I2S_RXD/I2S_RX_FS input hold after I2S_RX_BCLK	0	—	ns

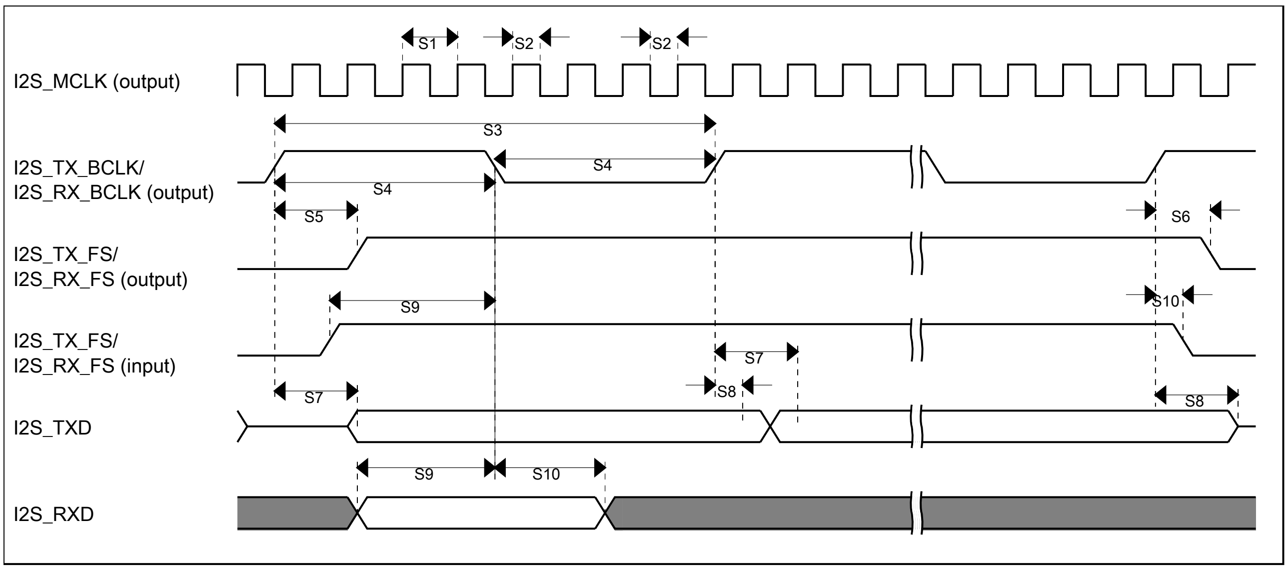

Figure 31. I2S/SAI timing — master modes

Table 53. I2S/SAI slave mode timing in VLPR, VLPW, and VLPS modes (full voltage range)

Num.	Characteristic	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
S11	I2S_TX_BCLK/I2S_RX_BCLK cycle time (input)	250	—	ns
S12	I2S_TX_BCLK/I2S_RX_BCLK pulse width high/low (input)	45%	55%	MCLK period
S13	I2S_TX_FS/I2S_RX_FS input setup before I2S_TX_BCLK/I2S_RX_BCLK	30	—	ns
S14	I2S_TX_FS/I2S_RX_FS input hold after I2S_TX_BCLK/I2S_RX_BCLK	11	—	ns
S15	I2S_TX_BCLK to I2S_TXD/I2S_TX_FS output valid	—		ns
S16	I2S_TX_BCLK to I2S_TXD/I2S_TX_FS output invalid	0	—	ns
S17	I2S_RXD setup before I2S_RX_BCLK	30	—	ns

Table continues on the next page...

144 QFP	100 LQFP	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7	ALT8	ALT9
32	23	VREFH	VREFH										
33	24	VREFL	VREFL										
34	25	VSSA	VSSA										
35	—	ADC1_SE16/CMP2_IN2/ADC0_SE22	ADC1_SE16/CMP2_IN2/ADC0_SE22										
36	—	ADC0_SE16/CMP1_IN2/ADC0_SE21	ADC0_SE16/CMP1_IN2/ADC0_SE21										
37	26	VREF_OUT/CMP1_IN5/CMP0_IN5/ADC1_SE18	VREF_OUT/CMP1_IN5/CMP0_IN5/ADC1_SE18										
38	27	DAC0_OUT/CMP1_IN3/ADC0_SE23	DAC0_OUT/CMP1_IN3/ADC0_SE23										
39	—	DAC1_OUT/CMP0_IN4/CMP2_IN3/ADC1_SE23	DAC1_OUT/CMP0_IN4/CMP2_IN3/ADC1_SE23										
40	28	XTAL32	XTAL32										
41	29	EXTAL32	EXTAL32										
42	30	VBAT	VBAT										
43	—	VDD	VDD										
44	—	VSS	VSS										
45	31	ADC0_SE17	ADC0_SE17	PTE24		UART4_TX		I2C0_SCL	EWM_OUT_b				
46	32	ADC0_SE18	ADC0_SE18	PTE25/x_LLWU_P21		UART4_RX		I2C0_SDA	EWM_IN			x_LLWU_P21	
47	33	DISABLED		PTE26	ENET_1588_CLKIN	UART4_CTS_b			RTC_CLKOUT	USB_CLKIN			
48	—	DISABLED		PTE27		UART4_RTS_b							
49	—	DISABLED		PTE28									

144 QFP	100 LQFP	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7	ALT8	ALT9
50	34	JTAG_ TCLK/ SWD_CLK/ EZP_CLK		PTA0	UART0_ CTS_b/ UART0_ COL_b	FTM0_CH5				JTAG_ TCLK/ SWD_CLK			EZP_CLK
51	35	JTAG_TDI/ EZP_DI		PTA1	UART0_RX	FTM0_CH6				JTAG_TDI			EZP_DI
52	36	JTAG_ TDO/ TRACE_ SWO/ EZP_DO		PTA2	UART0_TX	FTM0_CH7				JTAG_ TDO/ TRACE_ SWO			EZP_DO
53	37	JTAG_ TMS/ SWD_DIO		PTA3	UART0_ RTS_b	FTM0_CH0				JTAG_ TMS/ SWD_DIO			
54	38	NMI_b/ EZP_CS_b		PTA4/ LLWU_P3		FTM0_CH1				NMI_b		LLWU_P3	EZP_CS_b
55	39	DISABLED		PTA5	USB_ CLKIN	FTM0_CH2	RMII0_ RXER/ MII0_RXER	CMP2_ OUT	I2S0_TX_ BCLK	JTAG_ TRST_b			
56	40	VDD	VDD										
57	41	VSS	VSS										
58	—	DISABLED		PTA6		FTM0_CH3		CLKOUT		TRACE_ CLKOUT			
59	—	ADC0_ SE10	ADC0_ SE10	PTA7		FTM0_CH4				TRACE_D3			
60	—	ADC0_ SE11	ADC0_ SE11	PTA8		FTM1_CH0			FTM1_QD_ PHA	TRACE_D2			
61	—	DISABLED		PTA9		FTM1_CH1	MII0_RXD3		FTM1_QD_ PHB	TRACE_D1			
62	—	DISABLED		PTA10/ x_LLWU_ P22		FTM2_CH0	MII0_RXD2		FTM2_QD_ PHA	TRACE_D0		x_LLWU_ P22	
63	—	DISABLED		PTA11/ x_LLWU_ P23		FTM2_CH1	MII0_ RXCLK	I2C2_SDA	FTM2_QD_ PHB			x_LLWU_ P23	
64	42	CMP2_IN0	CMP2_IN0	PTA12	CAN0_TX	FTM1_CH0	RMII0_ RXD1/ MII0_RXD1	I2C2_SCL	I2S0_TXD0	FTM1_QD_ PHA			
65	43	CMP2_IN1	CMP2_IN1	PTA13/ LLWU_P4	CAN0_RX	FTM1_CH1	RMII0_ RXD0/ MII0_RXD0	I2C2_SDA	I2S0_TX_ FS	FTM1_QD_ PHB		LLWU_P4	
66	44	DISABLED		PTA14	SPI0_PCS0	UART0_TX	RMII0_ CRS_DV/ MII0_RXDV	I2C2_SCL	I2S0_RX_ BCLK	I2S0_TXD1			
67	45	DISABLED		PTA15	SPI0_SCK	UART0_RX	RMII0_ TXEN/ MII0_TXEN		I2S0_RXD0				

144 QFP	100 LQFP	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7	ALT8	ALT9
						UART0_ COL_b							
133	99	ADC0_ SE7b	ADC0_ SE7b	PTD6/ LLWU_P15	SPI0_PCS3	UART0_RX	FTM0_CH6	FB_AD0	FTM0_ FLT0	SPI1_ SOUT		LLWU_P15	
134	—	VSS	VSS										
135	—	VDD	VDD										

5.2 Unused analog interfaces

Table 54. Unused analog interfaces

Module name	Pins	Recommendation if unused
ADC	ADC0_DP1, ADC0_DM1, ADC1_DP1, ADC1_DM1, ADC0_DP0/ADC1_DP3, ADC0_DM0/ADC1_DM3, ADC1_DP0/ ADC0_DP3, ADC1_DM0/ADC0_DM3, ADC1_SE16/ADC0_SE22, ADC0_SE16/ADC0_SE21, ADC1_SE18	Ground
DAC [1]	DAC0_OUT, DAC1_OUT	Float
USB	VREGIN, USB0_GND, VOUT33[2]	Connect VREGIN and VOUT33 together and tie to ground through a 10 kΩ resistor. Do not tie directly to ground, as this causes a latch-up risk.
	USB0_DM, USB0_DP	Float

1. Unused DAC signals do not apply to all parts. See the Pinout section for details.
2. USB0_VBUS and USB0_GND are board level signals

5.3 K24 Pinouts

The below figure shows the pinout diagram for the devices supported by this document. Many signals may be multiplexed onto a single pin. To determine what signals can be used on which pin, see the previous section.

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